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c/o Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL). **SHI, Xiaoping** [NL/BE]; c/o Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL).

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(74) Agent: **DUIJVESTIJN, Adrianus, J.**; Philips Intellectual Property & Standards, Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL).

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(71) Applicant (*for all designated States except US*): **KONINKLIJKE PHILIPS ELECTRONICS N.V.** [NL/NL]; Groenewoudseweg 1, NL-5621 BA Eindhoven (NL).

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(71) Applicant (*for DE, FR, GB, JP only*): **INTERUNIVERSITAIR MICROELEKTRONICA CENTRUM VZW** [BE/BE]; Kapeldreef 75, B-3001 Leuven (BE).

(72) Inventors; and

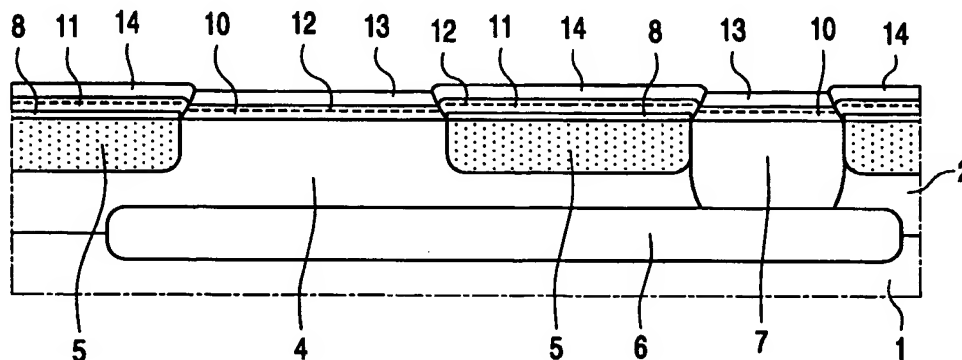
(75) Inventors/Applicants (*for US only*): **MAGNEE, Petrus, H., C.** [NL/BE]; c/o Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL). **DONKERS, Johannes, J., T., M.** [NL/NL];

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(54) Title: METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE



(57) Abstract: Method of manufacturing a semiconductor device, in which on a region of silicon oxide (5) situated next to a region of monocrystalline silicon (4) at the surface (3) of a semiconductor body (1), a non-monocrystalline auxiliary layer (8) is formed. The auxiliary layer is formed in two steps. In the first step, the silicon body is heated in an atmosphere comprising a gaseous arsenic compound; in the second step it is heated in an atmosphere comprising a gaseous silicon compound instead of said arsenic compound. Thus, the regions of silicon oxide are provided with an amorphous or polycrystalline silicon seed layer in a self-aligned manner.

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